

< C band internally matched power GaAs FET >

# MGFC36V3436

<u>3.4 – 3.6 GHz BAND / 4W</u>

#### DESCRIPTION

The MGFC36V3436 is an internally impedance-matched GaAs power FET especially designed for use in 3.4 - 3.6 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Class A operation

Internally matched to 50(ohm) system • High output power

- P1dB=4W (TYP.) @f=3.4 3.6GHz • High power gain
- GLP=13.5dB (TYP.) @f=3.4 3.6GHz • High power added efficiency
- P.A.E.=32% (TYP.) @f=3.4 3.6GHz • Low distortion [item -51]
- IM3=-45dBc (TYP.) @Po=25dBm S.C.L

#### APPLICATION

- item 01 : 3.4 3.6 GHz band power amplifier
- item 51 : 3.4 3.6 GHz band digital radio communication

## QUALITY

• IG

#### **RECOMMENDED BIAS CONDITIONS**

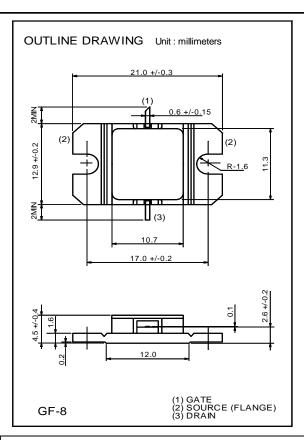
• VDS=10V • ID=1.2A • RG=100ohm

#### Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	3.75	А
IGR	Reverse gate current	-10	mA
IGF	Forward gate current	21	mA
PT *1	Total power dissipation	25	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

\*1 : Tc=25°C

#### Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	3.75	А
gm	Transconductance	VDS=3V,ID=1.1A	-	1	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=10mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=1.2A	35	37	-	dBm
GLP	Linear Power Gain	f=3.4 – 3.6GHz	11	13.5	-	dB
ID	Drain current		-	1.1	1.8	А
P.A.E.	Power added efficiency		-	32	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	5	6	°C/W

\*2 :item -51 ,2 tone test,Po=25dBm Single Carrier Level ,f=3.6GHz,delta f=5MHz

\*3 :Channel-case

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